

Title (en)

PROCESS FOR THE CONTINUOUS DIRECT SMELTING OF METALLIC LEAD FROM SULFIDIC LEAD CONCENTRATES

Publication

EP 0045531 B1 19840118 (DE)

Application

EP 81200502 A 19810512

Priority

DE 3029682 A 19800806

Abstract (en)

[origin: ES8203977A1] A molten bath consisting of a slag phase is maintained in an elongated horizontal reactor. The charge is fed into the reactor on one side thereof onto the molten bath in a melting zone so as to maintain an oxidation potential which causes metallic lead and slag to be formed. Reducing agent is introduced into the slag phase on the other side of the reactor in a reducing zone. To ensure that the bismuth contained in the charge is collected in the smallest possible quantity of crude lead, such an oxidation potential is maintained in the molten bath in the melting zone that the lead phase contains 0.05 to 2% by weight sulfur, the high-Bi primary lead which becomes available in that zone is separately tapped, and the low-Bi secondary lead which becomes available in the reducing zone is also separately tapped.

IPC 1-7

C22B 13/02; C22B 5/02; C22B 13/00; C22B 30/06

IPC 8 full level

C22B 13/06 (2006.01); **C22B 5/02** (2006.01); **C22B 13/00** (2006.01); **C22B 13/02** (2006.01); **C22B 13/08** (2006.01); **C22B 30/06** (2006.01)

CPC (source: EP KR US)

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DOCDB simple family (publication)

EP 0045531 A1 19820210; EP 0045531 B1 19840118; AR 228272 A1 19830215; AT E5901 T1 19840215; AU 544413 B2 19850523; AU 7380181 A 19820211; BR 8105030 A 19820420; CA 1171288 A 19840724; DE 3029682 A1 19820311; DE 3161936 D1 19840223; ES 502522 A0 19820401; ES 8203977 A1 19820401; FI 70730 B 19860626; FI 70730 C 19861006; FI 812264 L 19820207; IN 154428 B 19841027; JP H0158258 B2 19891211; JP S5757848 A 19820407; KR 830006453 A 19830924; KR 860000831 B1 19860702; MA 19236 A1 19820401; MX 155929 A 19880524; PH 17206 A 19840619; PL 232495 A2 19820413; US 4376649 A 19830315; YU 176881 A 19830930; YU 42020 B 19880430; ZA 813227 B 19820630; ZM 6981 A1 19830721

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